L Number	Hits	Search Text	DB	Time stamp
3	1237	257/316,326.ccls.	USPAT;	2003/05/13 15:15
_		·	US-PGPUB	į
4	960	257/316,326.ccls. and (opening or recess	USPAT;	2003/05/13 15:16
		or hole or trench or via) and memory	US-PGPUB	
5	115	(257/316,326.ccls. and (opening or recess	USPAT;	2003/05/13 15:17
		or hole or trench or via) and memory) and	US-PGPUB	1
		peripheral and sidewall		
6	83	((257/316,326.ccls. and (opening or recess	USPAT;	2003/05/13 15:17
		or hole or trench or via) and memory) and	US-PGPUB	
		peripheral and sidewall) and @ad<=20010112		

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	Туре	Hits	Search Text	DBs	Time Stamp
1	IS&R	ŗ-J	("6528328").PN.	USPAT; US-PGPUB	2003/05/13 15:05
2	BRS	97534	memory and peripheral	USPAT; US-PGPUB	2003/05/12 11:50
3	BRS	43147	memory same peripheral	USPAT; US-PGPUB	2003/05/12 11:50
4	BRS	29837	memory with peripheral	USPAT; US-PGPUB	2003/05/12 11:50
5	BRS	11685	(memory with peripheral) and semiconductor	USPAT; US-PGPUB	2003/05/12 11:51
9	BRS	7392	((memory with peripheral) and semiconductor) and transistor	USPAT; US-PGPUB	2003/05/12 11:51
7	BRS	3999	(((memory with peripheral) and semiconductor) and transistor) and (trench or hole or opening or recess)	USPAT; US-PGPUB	2003/05/12 11:52
8	BRS	1134	((((memory with peripheral) and semiconductor) and transistor) and (trench or hole or opening or recess)) and sidewalls	USPAT; US-PGPUB	2003/05/12 11:52
<u></u>	BRS	1134	((((memory with peripheral) and semiconductor) and transistor) and (trench or hole or opening or recess)) and sidewall	USPAT; US-PGPUB	2003/05/12 11:53
10	BRS	1018	((((memory with peripheral) and semiconductor) and transistor) and (trench or hole or opening or recess)) and sidewall) and source and drain	USPAT; US-PGPUB	2003/05/12 11:53
11	BRS	950	(((((memory with peripheral) and semiconductor) and transistor) and (trench or hole or opening or recess)) USPAT; and sidewall) and source and drain) and (etching or removing)	USPAT; US-PGPUB	2003/05/12 11:54

	Туре	Hits	Search Text	DBs	Time Stamp
12	BRS	640	((((((memory with peripheral) and semiconductor) and transistor) and (trench or hole or opening or recess)) and sidewall) and source and drain) and (etching or removing) and @ad<=20010112	USPAT; US-PGPUB	2003/05/12 14:01
13	BRS	640	((((((memory with peripheral) and semiconductor) and transistor) and (trench or hole or opening or recess)) and sidewall) and source and drain) and (etching or removing) and (ad<=20010112	USPAT; US-PGPUB	2003/05/12 14:02
14	IS&R	1	("6316799").PN.	USPAT; US-PGPUB	2003/05/13 07:49
15	BRS	1016	245,258	USPAT; US-PGPUB	2003/05/13 09:30
16	BRS	867	41,245,258. s or hole o	USPAT; US-PGPUB	2003/05/13 09:30
17	BRS	806	'241,245,258.ccls. and (opening orse or hole or trench or via)) and:	USPAT; US-PGPUB	2003/05/13 09:31
18	BRS	715	1,245, s or h ry) an	USPAT; US-PGPUB	2003/05/13 09:31
13	BRS	360	41,245 s or h ry) an al	USPAT; US-PGPUB	2003/05/13 09:31
20	BRS	286	((((438/241,245,258.ccls. and (opening or recess or hole or trench or via)) and memory) and transistor) and peripheral) and @ad<=20010112	USPAT; US-PGPUB	2003/05/13 09:31
21	BRS	580	259,26	USPAT; US-PGPUB	2003/05/13 09:30
22	BRS	504	438/259,266.ccls. and (opening or recess or hole or trench or via)	USPAT; US-PGPUB	2003/05/13 09:31

	Туре	Hits	Search Text	DBs	Time Stamp
23	BRS	431	ccls. and (opening or e or trench or via)) and	USPAT; US-PGPUB	2003/05/13 09:31
24	BRS	349	((438/259,266.ccls. and (opening or recess or hole or trench or via)) and memory) and transistor	USPAT; US-PGPUB	2003/05/13 09:31
25	BRS	106		USPAT; US-PGPUB	2003/05/13 09:31
56	BRS	78	((((438/259,266.ccls. and (opening or recess or hole or trench or via)) and memory) and transistor) and peripheral) and @ad<=20010112	USPAT; US-PGPUB	2003/05/13 09:31
27	BRS	5.4	(((((438/259,266.ccls. and (opening or recess or hole or trench or via)) and memory) and transistor) and peripheral) and @ad<=20010112) not ((((438/241,245,258.ccls. and (opening or recess or hole or trench or via)) and memory) and transistor) and peripheral) and @ad<=20010112)	USPAT; US-PGPUB	2003/05/13 09:32